

Three Phase Diode + Thyristor

DFA75BA80/160

UL; E76102

Features

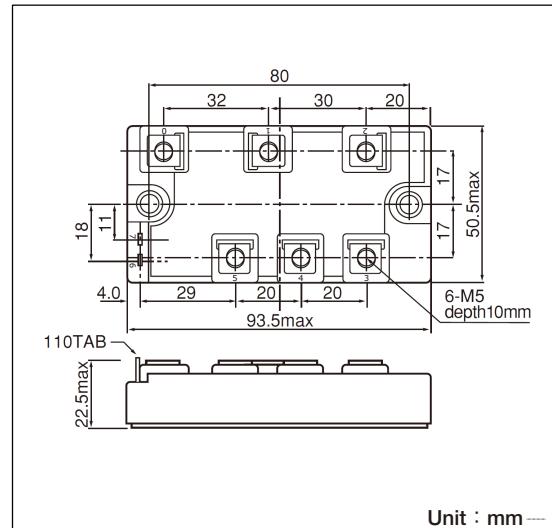
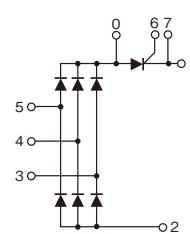
Power Module, DFA75BA, is complex isolated module which is designed for rash current circuit.

It contains six diodes connected in a three phase bridge configuration, and a thyristor connected to a direct current line.

- This Module is designed very compactly. Because diode module and thyristor put together.
- This Module is also isolated type between electrode terminal and mounting base. So you can put this Module and other one together in a same fin.

Applications

- Inverter for AC or DC motor control / Current stabilized power supply / Switching power supply



Unit : mm ---

● DIODE

(T_j=25°C unless otherwise specified)

| Item | Symbol | Unit | DFA75BA80 | DFA75BA160 |
|-------------------------------------|------------------|------|-----------|------------|
| Repetitive Peak Reverse Voltage | V _{RRM} | V | 800 | 1600 |
| Non-Repetitive Peak Reverse Voltage | V _{RSM} | V | 960 | 1700 |

| Item | Symbol | Unit | Ratings | Conditions |
|-------------------------------------|----------------------|------|-------------|---|
| Output Current (D.C.) | I _D | A | 75 | Three phase full wave, T _C =101°C |
| Surge forward current | I _{FSM} | A | 910/1000 | 1/2cycle, 50/60Hz, peak value, non-repetitive |
| Repetitive Peak Reverse Current,max | I _{RRM} | mA | 8 | T _j =150°C, V _R =V _{RRM} |
| Forward Voltage Drop,max | V _{FM} | V | 1.30 | I _F =75A, Inst. measurement |
| Operating Junction Temperature | T _j | °C | -40 to +150 | |
| Thermal Resistance,max | R _{th(j-c)} | °C/W | 0.25 | Junction to Case (Total) |

● THYRISTOR

(T_j=25°C unless otherwise specified)

| Item | Symbol | Unit | DFA75BA80 | DFA75BA160 |
|-------------------------------------|------------------|------|-----------|------------|
| Repetitive Peak Reverse Voltage | V _{RRM} | V | 800 | 1600 |
| Non-Repetitive Peak Reverse Voltage | V _{RSM} | V | 960 | 1700 |
| Repetitive Peak Off-State Voltage | V _{DRM} | V | 800 | 1600 |

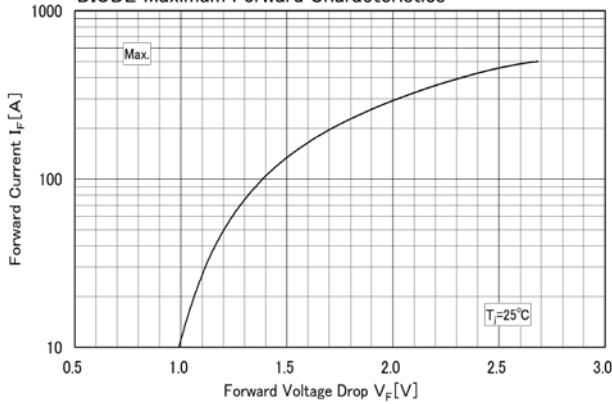
| Item | Symbol | Unit | Ratings | Conditions |
|---|----------------------|------------------|-------------|---|
| Average On-State Current | I _{T(AV)} | A | 75 | Single phase half wave. 180° conditon, T _C =99°C |
| Surge On-State Current | I _{TSM} | A | 910/1000 | 1/2cycle, 50/60Hz, Peak value, non-repetitive |
| I ² t(for fusing) | I ² t | A ² S | 4150 | Value for one cycle of surge current |
| Critical Rate of Rise of On-State Current | di/dt | A/μs | 150 | I _G =100mA V _D =1/2V _{DRM} dI _G /dt=0.1A/μs |
| Operating Junction Temperature | T _j | °C | -40 to +135 | |
| Repetitive Peak Off-State Current,max. | I _{DRM} | mA | 60 | T _j =135 °C, V _D =V _{DRM} |
| Repetitive Peak Reverse Current,max. | I _{RRM} | mA | 60 | T _j =135 °C, V _R =V _{RRM} |
| Peak On-State Voltage,max. | V _{TM} | V | 1.20 | I _T = 75A Inst. measurement |
| Gate Trigger Current,max. | I _{GT} | mA/V | 70 | I _T =1A V _D =6V T _j =25°C |
| Gate Trigger Voltage,max. | V _{GT} | mA/V | 3 | I _T =1A V _D =6V T _j =25°C |
| Critical Rate of Rise of Off-State Voltage,min. | dv/dt | V/μs | 500 | T _j =125°C V _D =2/3V _{DRM} Exponential wave |
| Holding Current | I _H | mA | 100 | T _j =25°C |
| Latching Current | I _L | mA | 80 | T _j =25°C |
| Thermal Resistance,max | R _{th(j-c)} | °C/W | 0.40 | Junction to Case |

● GENERAL

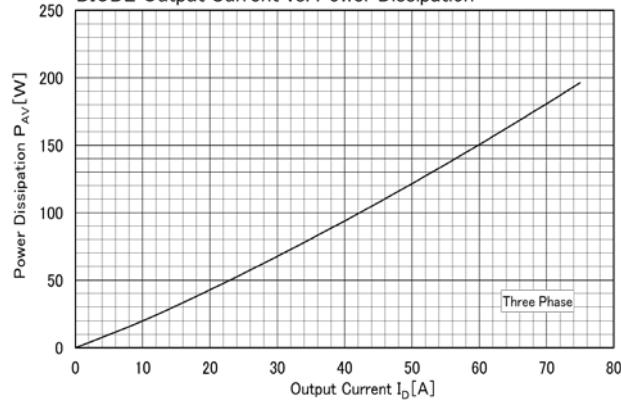
(T_J=25°C unless otherwise specified)

| Item | Symbol | Unit | Ratings | Conditions |
|--------------------------------------|--------------------------------|-----------------|--------------------|--|
| Isolation Breakdown Voltage (R.M.S.) | V _{ISO} | V | 2500 | A.C., 1 minute |
| Storage Temperature | T _{stg} | °C | -40 to +125 | |
| Thermal Resistance,max | R _{th(c-f)} | °C/W | 0.10 | Case to fin |
| Mounting Torque | Mounting (M5) Terminal (M5) | N·m (kgf·cm) | 2.7(28) 2.7(28) | Recommended Value 1.5 to 2.5 (15 to 25) Recommended Value 1.5 to 2.5 (15 to 25) |
| Mass | | g | 150 | Typical value |

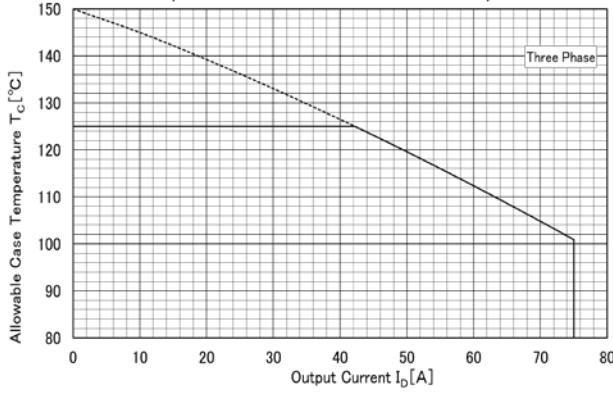
DIODE Maximum Forward Characteristics



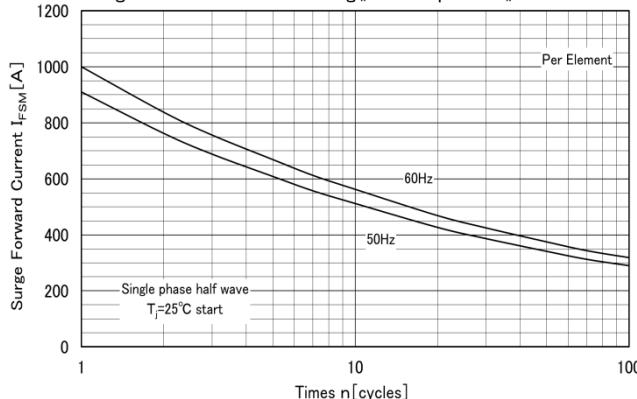
DIODE Output Current vs. Power Dissipation



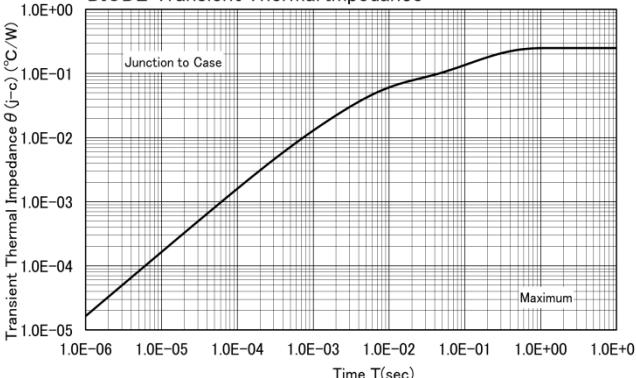
DIODE Output Current vs. Allowable Case Temperature



Surge Forward Current Rating《Non-Repetitive》



DIODE Transient Thermal Impedance



SCR Gate Characteristics

